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Complementary Silicon High-Power Transistors

... PowerBase complementary transistors designed for high power audio, stepping motor and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc-to-dc converters, inverters, or for inductive loads requiring higher safe operating area than the 2N3055 and MJ2955.

- Current-Gain — Bandwidth-Product @ $I_C = 1.0$ Adc
 $f_T = 0.8$ MHz (Min) — NPN
 $= 2.2$ MHz (Min) — PNP
- Safe Operating Area — Rated to 60 V and 120 V, Respectively

*MAXIMUM RATINGS

Rating	Symbol	2N3055A MJ2955A	MJ15015 MJ15016	Unit
Collector-Emitter Voltage	V_{CE0}	60	120	Vdc
Collector-Base Voltage	V_{CB0}	100	200	Vdc
Collector-Emitter Voltage Base Terminals Eased	V_{CEV}	100	200	Vdc
Emitter-Base Voltage	V_{EB0}	7	7	Vdc
Collector Current — Continuous	I_C	15	15	A
Base Current	I_B	7.0	7.0	A
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	115 0.65	180 1.03	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.52	0.98	°C/W

* Indicates JEDEC Registered Data. (2N3055A)

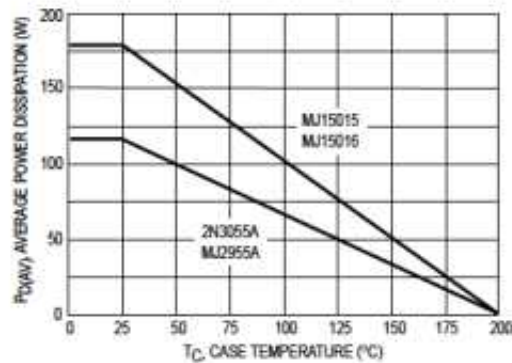


Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 1

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NPN
2N3055A

MJ15015*

MJ2955A
PNP
MJ15016*

*Motorola Preferred Device

15 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
60, 120 VOLTS
115, 180 WATTS



CASE 1-07
TO-18A
(D-3)





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Maximum Ratings[edit]The maximum collector-to-emitter voltage for the 2N3055, like other transistors, depends on the resistance path the external circuit provides between the base and emitter of the transistor; with 100 ohms a 70 volt breakdown rating, VCER, and the Collector-Emitter Sustaining voltage, VCEO(sus), is given by ON Semiconductor.

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2N3055 SILICON NPN TRANSISTOR SGS-THOMSONPREFERRED SALESTYPE DESCRIPTION The 2N3055 is a silicon epitaxial-base NPN transistor in JedecTO-3 metalcase.. 1Specifications2HistorySpecifications[edit]The exact performance characteristics depend on the manufacturer and date; before the move to the epitaxial base version in the mid-1970s the fT could be as low as 0.. 5 MHzPackaged in a TO-3 case style, it is a 15 amp, 60 volt (or more, see below), 115 watt power transistor with a β (forward current gain) of 20 to 70 at a collector current of 4 A (this may be 100 to 200 when testing using a multimeter[6]).. INTERNAL SCHEMATIC DIAGRAM October1995 ABSOLUTE MAXIMUM RATINGS Symbol 21 rows 2N3055 Datasheet, 2N3055 PDF, 2N3055 Data sheet, 2N3055 manual, 2N3055 pdf, 2N3055.

datasheet

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[1] Its numbering follows the JEDEC standard [2] It is a transistor type of enduring popularity.. ST Microelectronics 2n3055 Datasheet Pdf Download2n3055 Npn Transistor DatasheetTransistor 2n3055 Datasheet PdfThe 2N3055 is a silicon NPNpowertransistor intended for general purpose applications.. [3][4][5]2N3055 transistor mounted on an aluminum heat sink A mica insulator electrically isolates the transistor case from the heatsink.. Manufacturers rarely specify the VCES voltage rating for the 2N3055 [download Microsoft Word 2017](#)

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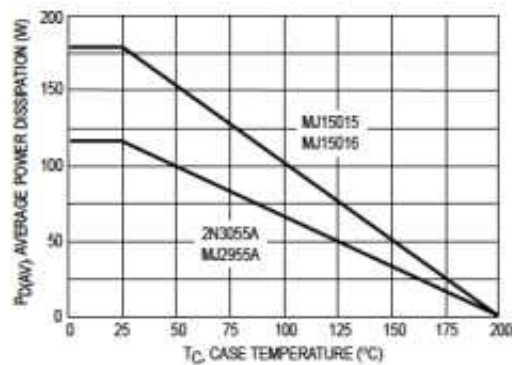


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115, 180 WATTS



CASE 1-07
TO-18A
(D-3)



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8 MHz, for example manufacturerDataVCEOVCBOVCER (100 ohms)ICIBPD @ TC=25 deg hfe (pulsed test)fTRCA196760 VCEO(sus)100 VCBO70 VCER(sus)15A7A115W20-70 (at IC = 4Apulsed)not givenON-Semiconductor2005[6]60 VCEO100 VCBO70 VCER15A (continuous)7A115W20-70 (at IC = 4A)2. [كيف اعمل فيديو من النت حالة الواتس اب](#).

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It is intended for power switching circuits, series and shunt regulators, output stages and high fidelity amplifiers.. 2N3055 datasheet, 2N3055 pdf, 2N3055 data sheet, datasheet, data sheet, pdf, Boca Semiconductor Corporation, COMPLEMENTARY SILICON POWER TRANSISTORS.. It was introduced in the early 1960s by RCA using a homotaxial power transistor process, transitioned to an epitaxial base in the mid-1970s.. All the part names for which the file 4079 pdf is a datasheet LM317 LM339 MAX232 NE555 LM324 8051 7805 2N3055 LM358 2N2222.. It often has a transition frequency of around 3 0 MHz and 6 MHz is typical for the 2N3055A; at this frequency the calculated current gain (beta) drops to 1, indicating the transistor can no longer provide useful amplification in common emitter configuration.. The frequency at which gain begins to drop off may be much lower, see below 2N3055 transistor internals.. Sometimes the 100 VCBO breakdown voltage (the maximum voltage between collector and base, with the emitter open, an unrealistic arrangement in practical circuits) is given as the only voltage rating, which can cause confusion. ae05505a44 [Optimize Mac For Gaming](#)

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